

L Number	Hits	Search Text	DB	Time stamp
1	1	("6127099").PN.	USPAT;	2003/10/02
2	1	("6287750").PN.	US-PGPUB	13:06
3	2339	photosensitive with polyimide	USPAT;	2003/10/02
4	515	(photosensitive with polyimide) and	US-PGPUB	13:51
5	47	(etching with polyimide)	USPAT;	2003/10/02
6	36	((photosensitive with polyimide) and	US-PGPUB	14:39
7	925	(etching with polyimide)) and ((damage or	USPAT;	2003/10/02
8	71	damaging or hardened) with polyimide)	US-PGPUB	14:39
9	1	((photosensitive with polyimide) and	USPAT;	2003/10/02
10	32	((photosensitive with polyimide) and	US-PGPUB	14:41
11	21	((photosensitive with polyimide) and	USPAT;	2003/10/02
12	5	((photosensitive with polyimide) and	US-PGPUB	14:41
13	1026	photosensitive with polyimide	EPO;	2003/10/02
14	59	(photosensitive with polyimide) and	DERWENT	14:44
15	2	(etching with polyimide)	EPO;	2003/10/02
16	6	((photosensitive with polyimide) and	DERWENT	14:44
17	1146	(etching with polyimide)) and (hardened	EPO;	2003/10/02
18	131	with polyimide)	DERWENT	14:40
19	5	((photosensitive with polyimide) and	USPAT;	2003/10/02
20	6273	(etching with polyimide)) and (fluorine	US-PGPUB	14:41
21	595	with polyimide)	USPAT;	2003/10/02
22	104	((photosensitive with polyimide) and	US-PGPUB	15:05
23	95	(etching with polyimide)) and (fluorine	USPAT;	2003/10/02
24	4315	with polyimide)) and @ad<20010105	US-PGPUB	14:45
25	437	photosensitive with polyimide	USPAT;	2003/10/02
26	299	(photosensitive with polyimide) and	US-PGPUB	14:47
27	85	(etching with polyimide)	JPO	2003/10/02
28	76	((photosensitive with polyimide) and	JPO	14:47
29		(etching with polyimide)) and hardened	JPO	14:47
		photosensitive with polyimide	JPO	2003/10/02
		(photosensitive with polyimide) and	JPO	14:47
		(etching with polyimide)	JPO	2003/10/02
		((photosensitive with polyimide) and	JPO	14:47
		(etching with polyimide)) and hardened	JPO	2003/10/02
		photosensitive with polyimide) and	JPO	14:46
		etching and hardened	JPO	14:46
		photosensitive same polyimide	JPO	2003/10/02
		(photosensitive same polyimide) and	JPO	15:03
		(etching same polyimide)	JPO	2003/10/02
		((photosensitive same polyimide) and	JPO	14:47
		(etching same polyimide)) and hardened	JPO	15:04
		etching same photosensitive	USPAT;	2003/10/02
		(etching same photosensitive) and	US-PGPUB	15:05
		hardened	USPAT;	2003/10/02
		etching same photosensitive same hardened	US-PGPUB	15:18
		(etching same photosensitive same	USPAT;	2003/10/02
		hardened) and @ad<20010105	US-PGPUB	15:05
		photosensitive with photoresist	USPAT;	2003/10/02
		(photosensitive with photoresist) and	US-PGPUB	15:21
		hardened	USPAT;	2003/10/02
		((photosensitive with photoresist) and	US-PGPUB	15:21
		hardened) and etching	USPAT;	2003/10/02
		(photosensitive with photoresist) same	US-PGPUB	15:18
		hardened	USPAT;	2003/10/02
		((photosensitive with photoresist) same	US-PGPUB	15:21
		hardened) and @ad<20010105	USPAT;	2003/10/02
			US-PGPUB	15:21

US-PAT-NO: 6060728
DOCUMENT-IDENTIFIER: US 6060728 A
TITLE: Organic light emitting device
structure and process

----- KWIC -----

Application Filing Date - AD (1):
19980615

Detailed Description Text - DETX (16):

With reference to FIG. 6, in a second alternative embodiment of the invention, the upper organic layer 540 may comprise a hardened top layer of organic material 542. If the upper organic layer 540 comprises photoresist or photosensitive polyamide, for example, then the hardened top layer 542 may be formed by using either a chemical process or a radiation process. The hardened top layer 542 may act as a mask for a subsequent plasma process that may result in the device profile shown in FIG. 6. The organic stack 300 may then be evaporated into the channel 502 at a larger angle than the electron injector layer 402. This may prevent the electron injector layer 402 from shorting to the hole injector layer 200.

US-PAT-NO: 5472774
DOCUMENT-IDENTIFIER: US 5472774 A
TITLE: Photolithography test structure

----- KWIC -----

Application Filing Date - AD (1):
19940819

Brief Summary Text - BSTX (5):

Lithography, also referred to as photolithography, and sometimes as pattern printing, is a processing methodology by which a pattern is transferred to a target surface or substrate. A pattern is transferred from a mask onto a substrate, which involves the steps of coating, exposing and developing photosensitive resist placed across the substrate. The substrate is first prepared for patterning by removing foreign materials from the substrate surface. An oxide such as, e.g., SiO₂ is then allowed to grow across the clean substrate. Photolithography processing may begin by placing the photosensitive material, often called "photoresist" or "resist", across the prepared substrate surface. Spin coating a liquid photoresist across the substrate is well known, and provides a suitable thin film of protective covering upon the substrate area. The mask is then placed in contact with the photoresist or in close proximity with the photoresist. A light source is configured behind the mask allowing radiation to pass through select portions of the mask and onto the photoresist. Emitted radiation is preferably within the ultraviolet (UV) region. A pattern of photoresist

US-PAT-NO: 5916453
DOCUMENT-IDENTIFIER: US 5916453 A
TITLE: Methods of planarizing structures on
wafers and substrates by polishing

----- KWIC -----

Application Filing Date - AD (1):
19960920

Detailed Description Text - DETX (14):

In constructed examples of this embodiment which are employed to manufacture multi-layer interconnect boards, planarizing layer 120 comprises a polyimide material, which is cured or imidized (i.e., hardened) before photosensitive layer 116 is removed, and preferably before layer 116 is formed. This enables the use of a standard solvent to removed layer 116 without removing layer 120, and the imidization increases the resistance of layer 120 to the solvent. Also, polish-stop layer 122 preferably comprises tungsten, which can be readily removed by a hydrogen peroxide solution which does not damage either of layers 116 and 120, and copper is used as the material which fills apertures 117 to form post 118.

Detailed Description Text - DETX (22):

The removal rate of tungsten was found to be lower in acidic slurries than in alkaline slurries, and this is believed to be due to the formation of an oxide layer over the tungsten in acidic (low pH) slurries, This oxide layer retards the chemical-mechanical polishing of tungsten.

US-PAT-NO: 6074561
DOCUMENT-IDENTIFIER: US 6074561 A
TITLE: Apparatus and method for recovering
photoresist developers and strippers

----- KWIC -----

Application Filing Date - AD (1):
19980519

Brief Summary Text - BSTX (3):

In the printed circuit, semiconductor, chemical milling, and printing industries, a photosensitive emulsions known as a photoresist is applied to various substrates. A phototool or mask defining a pattern is applied over the photoresist. Exposure of a negative-working photoresist through the mask to radiation, for example ultraviolet light, results in a pattern of hardened polymer emulsion in the exposed area. Positive-working photoresists are also sometimes used, and result in a pattern of hardened photoresist in the non-exposed area.